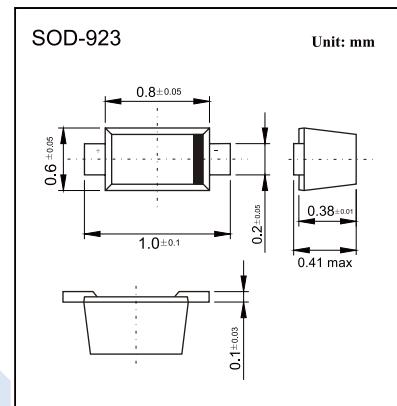
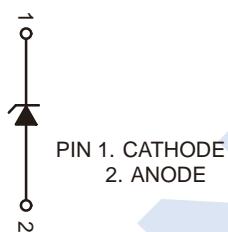


## ESD Protection Diodes

### ESD9C5.0ST5G

#### ■ Features

- Low Leakage
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Stand-off Voltage: 5 V
- IEC61000-4-2 Level 4 ESD Protection



#### ■ Absolute Maximum Ratings Ta = 25

Parameter	Symbol	Value	Unit
Clamping Voltage @ I <sub>PP</sub>	V <sub>C</sub>	5.0	V
Working Peak Reverse Voltage	V <sub>RWM</sub>	5.0	V
Breakdown Voltage @ I <sub>T</sub>	V <sub>BR</sub>	11.0	V
Forward Voltage @ I <sub>F</sub>	V <sub>F</sub>	1.1	V
Forward Current	I <sub>F</sub>	10	mA
Test Current	I <sub>T</sub>	1.0	mA
Maximum Reverse Leakage Current @ V <sub>RWM</sub>	I <sub>R</sub>	0.5	uA
Total Power Dissipation on FR-5 Board @ T <sub>A</sub> = 25°C	P <sub>D</sub>	150	mW
Peak Power Dissipation	P <sub>pk</sub>	150	W
Max. Capacitance @ V <sub>R</sub> = 0 and f = 1 MHz	C	6.2	pF
Lead Solder Temperature – Maximum (10 Second Duration)	T <sub>L</sub>	260	°C
Junction Temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>sig</sub>	-55 to +150	°C

## ESD Protection Diodes

### ESD9C5.0ST5G

#### ■ Electrical Characteristics $T_a = 25^\circ C$

Device	Device Marking	$V_{RWM}$ (V)		$I_R$ ( $\mu A$ ) @ $V_{RWM}$	$V_{BR}$ (V) @ $I_T$ *1	$I_T$	$C$ (pF) *2	$C$ (pF) *2
		Max	Max		Min	mA	Typ	Max
ESD9C5.0ST5G	P	5.0	0.5	11.0	1.0	6.0	6.2	

\*1. VBR is measured with a pulse test current  $I_T$  at an ambient temperature of  $25^\circ C$ .

\*2. Capacitance at  $f = 1$  MHz,  $VR = 0$  V,  $TA = 25^\circ C$ .

#### ■ Marking

Marking	P
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#### ■ Typical Characteristics

